

Abstract Submitted  
for the MAR15 Meeting of  
The American Physical Society

**IR Ellipsometry on RF sputtered Permalloy Oxide thin films<sup>1</sup>**

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<sup>1</sup>This work was partly funded by National Science Foundation (DMR-1104934). Use of the facilities of the CINT at Sandia National Lab is acknowledged.

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Date submitted: 15 Nov 2014

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